

# Tailoring the Mesoscopic Structure of Superconductors to Boost $T_c$ beyond the Present Limits

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# Acknowledgements:



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# The Road to Room-Temperature Superconductivity

For Fame:

- $> T_{c} = 300 \text{ K}$
- ➤ no layered cuprate

For Fortune:

- *≻ T*<sub>c</sub> > 500 K
- $> J_e (350 \text{ K}) > 10^4 \text{ A/cm}^2 \text{ in 5 T}$
- > ductile, robust, good thermal properties
- > good Josephson junctions
- > environmentally friendly compound
- ➤ available in large quantities

> < 20 € kA/m</p>

### Two Breakthrough Developments in Materials Fabrication

1) Bulk can be fabricated with film techniques



#### link to Gurevich, Grant

### Two Breakthrough Developments in Materials Fabrication

1) Bulk can be fabricated with film techniques

2) Fabrication of new materials that are designed on the unit cell level



Y. Zhu (2000)



link to Bozovich

Models and theories usually focus on single phase materials the limits and problems that have been identified predominantly refer to single phases

I) New phases

Putting atoms in place by nano-fabrication (e.g. by AFM) or epitaxial procedures

link to Grant, Uchida, Bozovic

### II) Boosting T<sub>c</sub> by Optimizing the Mesoscopic Structure

Granular Al:



#### G. Deutscher:

"New Superconductors: From Granular to High-T<sub>c</sub>" (2005)

### II) Boosting $T_c$ by Optimizing the Mesoscopic Structure

1) Kresin Effect: nanoclusters with number of electrons close to magic

Flux Periodicity of Small Superconducting Rings

BdG calculations of superconducting rings with diameter *D* at *T*=0:

- > magnetic flux may Doppler-shift states beyond  $E_{\rm F}$
- > state population of the condensate may change with flux
- flux periodicity of superconducting rings:

s-wave: h/2e for  $D \ge \xi$ , h/e for  $D \le \xi$ d-wave: h/e

the 2 of *h*/2*e* is a consequence of the *s*-wave symmetry (no nodes)

F. Loder, A. Kampf, T. Kopp, J.M., C.W. Schneider, Y.S. Barash, submitted

### II) Boosting $T_c$ by Optimizing the Mesoscopic Structure

1) Kresin Effect: nanoclusters with number of electrons close to magic

### II) Boosting $T_c$ by Optimizing the Mesoscopic Structure

- 1) Kresin Effect: nanoclusters with number of electrons close to magic
- 2) For superconductors with self-organized real space structure: support this internal structure by starting with an artificial microstructure, reduction of the energy costs of phase separation

3) High-T<sub>c</sub> at interfaces

links to Rice, Scalapino, Geballe, Kresin, Kivelson, Bozovic

### Using Interfaces to Enhance T<sub>c</sub>



Interfaces to:

- 1) stabilize superconducting phase / suppress phase transitions
- 2) optimize doping
  - spatially separate doping layer from layer with pair interaction (see HTS)

#### 4 JUNE 1990

#### Nonhomogeneous Charge Distribution in Layered High- $T_c$ Superconductors

M. Di Stasio,<sup>(1)</sup> K. A. Müller,<sup>(2)</sup> and L. Pietronero<sup>(1)</sup>

<sup>(1)</sup>Dipartimento di Fisica, Universitá di Roma "La Sapienza," Piazzale Aldo Moro, 2, 00185 Roma, Italy <sup>(2)</sup>IBM Research Division, Zurich Research Laboratory, Saumerstrasse 4, 8803 Ruschlikon, Switzerland



#### link to Uchida



### Field Effect Doping of *a*-axis Oriented Infinite Layer Compounds



collaboration with S.I. Lee, Pohang University

### Doping of Compounds with Large number of CuO<sub>2</sub> planes



collaboration with S.I. Lee, Pohang University

### Doping of Compounds with Large number of CuO2 planes

### Photodoping of $HgBa_2Ca_3Cu_4O_x$



collaboration with S.I. Lee, Pohang University

### Using Interfaces to Enhance $T_c$



Interfaces to:

- 1) stabilize superconducting phase / suppress phase transitions
- 2) optimize doping
  - spatially separate doping layer from layer with pair interaction (see HTS)
- 3) create novel electronic phases:
  - correlation parameters at interfaces different from those of bulk -

### Interfaces to Correlated Electron Systems

### G. Sawatzky, A. Millis, J.M.

standard metal



J. M. in "Thin Films and Heterostructures for Oxide Electronics" Springer (2005)

### Using Interfaces to Enhance T<sub>c</sub>



Interfaces to:

- 1) stabilize superconducting phase / suppress phase transitions
- 2) optimize doping
  - spatially separate doping layer from layer with pair interaction (see HTS)
- 3) create novel electronic phases:
  - correlation parameters at interfaces different from those of bulk -
- 4) use interface chemistry / induce defects
- 5) create *E* and *B* fields, break inversion symmetry
- 6) spatially separate pairing interaction from flow of carriers

#### Possibility of Synthesizing an Organic Superconductor\*

W. A. LITTLE

Department of Physics, Stanford University, Stanford, California (Received 13 November 1963; revised manuscript received 27 January 1964)

London's idea that superconductivity might occur in organic macromolecules is examined in the light of the BCS theory of superconductivity. It is shown that the criterion for the occurrance of such a state can be met in certain organic polymers. A particular example is considered in detail. From a realistic estimation of the matrix elements and density of states in this polymer it is concluded that superconductivity should occur even at temperatures well above room temperature. The physical reason for this remarkable high transition temperature is discussed. It is shown further that the superconducting state of these polymers should be distinguished by certain unique chemical properties which could have considerable biological significance.

PHYSICAL REVIEW B

#### VOLUME 7, NUMBER 3

1 FEBRUARY 1973

#### Model for an Exciton Mechanism of Superconductivity<sup>\*</sup>

David Allender,<sup>†</sup> James Bray, and John Bardeen Department of Physics and Materials Research Laboratory, University of Illinois, Urbana, Illinois 61801 (Received 7 August 1972)

The exciton mechanism of superconductivity is discussed with respect to a particular model, a thin metal layer on a semiconductor surface. In this model, the metal electrons at the Fermi surface tunnel into the semiconductor gap where they interact with virtual excitons, producing a net attractive interaction among the electrons in direct analogy with the phonon mechanism of superconductivity. The physical requirements for successful realization of the exciton mechanism in a metal-semiconductor system are explored in detail, and the relevant parameters are described. Estimates are made for electron tunneling and band-bending effects, and an electron-exciton coupling constant is defined and estimated. Finally, an appropriately modified integral equation for the superconducting energy gap is solved numerically to yield transition temperatures both for a pure-exciton mechanism and for the exciton and phonon mechanisms acting simultaneously.

#### ON SURFACE SUPERCONDUCTIVITY

V. L. GINZBURG

P.N.Lebedev Institute of Physics, USSR Academy of Sciences, Moscow

Received 21 October 1964

The superconductivity usually considered is a three-dimensional effect of ordering. However, a two-dimensional (surface) superconductivity is also conceivable [1] just as, for instance, a surface ferromagnetism [2].

We can consider two types of surface super-

exchange by surface photons, variation of screening, etc. The second case of surface superconductivity is connected with the transition into the superconducting state of electrons in surface states of the crystal. In that case, of course, the crystal may be non-metallic in the volume; if, however, the surface band is filled only partially, we shall deal, so to say, with a surface metal. conductivity. We assume in the first case that a resulting attraction takes place between electrons in the layer of metal near to the surface, while repulsion prevails in the volume. Such a difference may be connected with the fact that the interaction varies near the surface, for instance, due to the





interface, pairingquantum well layer2-DEG

Model System:

mobile charge carriers at the interface,

pairing by virtual polarizations of the adjacent layer



mobile electrons (TiO<sub>2</sub>)

### polarizable dipoles (SrTiO<sub>3</sub>)

V. Koerting et al., PRB 71, 104510 (2005)

#### Model System:



 $H_{\text{tot}} = H_t + H_{e-e} + H_{\mu} + H_{2l} + H_{\text{ext}} + H_{\text{int}}$ 

$$H_t = -t \sum_{\langle i,j \rangle,\sigma} c^{\dagger}_{i,\sigma} c_{j,\sigma}$$

$$H_{e-e} = U \sum_{i} n_{i,\uparrow} n_{i,\downarrow} + V \sum_{\langle i,j \rangle} (1 - n_i)(1 - n_j)$$

$$H_{\mu}=-\mu\sum_{i,\sigma}c_{i,\sigma}^{\dagger}c_{i,\sigma}$$

$$H_{2\mathrm{l}} = rac{1}{2} \Delta_{pd} \sum_i (p_i^\dagger p_i - d_i^\dagger d_i)$$

$$H_{ ext{ext}} = arepsilon_g \sum_i (p_i^\dagger d_i - d_i^\dagger p_i)$$

$$H_{\mathrm{int}} = V_{pd} \sum_{i,\sigma} c^{\dagger}_{i,\sigma} c_{i,\sigma} (p^{\dagger}_i d_i + d^{\dagger}_i p_i)$$

V. Koerting et al., PRB 71, 104510 (2005)

#### Model System:



*t* = 100 meV

V. Koerting et al., PRB 71, 104510 (2005)







n = 4.5

A<sub>4.5</sub>B<sub>4.5</sub>O<sub>15.5</sub>

**ABO**<sub>3.444</sub>



 $A_5B_5O_{17}$ 

**ABO**<sub>3.40</sub>





# SrNbO<sub>3.4</sub>







F. Lichtenberg

### $A_n B_n O_{3n+2} = ABO_x$ Niobates and Titanates



SrNbO<sub>3.45</sub>

F. Lichtenberg, D. Widmer, J.G. Bednorz, T. Williams, A. Reller, Z. Phys. B 84, 369 (1991)

### Electric Susceptibility of SrNbO<sub>3.41</sub> along *c*-axis



V. Bobnar et al., Phys. Rev. B (2002)



F. Lichtenberg et al., Prog. Solid State Chem. 29, 1 (2001)

## The LaAlO<sub>3</sub> / SrTiO<sub>3</sub> Interface



LaAlO<sub>3</sub>: band insulator  $\Delta = 5.6 \,\mathrm{eV}, \ \kappa = 24$ 

SrTiO<sub>3</sub>:

band insulator

 $\Delta = 3.2 \,\mathrm{eV}, \ \kappa \left( E = 0, \, 4.2 \,\mathrm{K} \right) = 2 \times 10^4$ 

quantum paraelectric

link to Bozovic

A. Ohtomo, H. Hwang, Nature <u>427</u>, 423 (2004)

### AFM Images of LaAlO<sub>3</sub> (5 uc) / SrTiO<sub>3</sub> Heterostructure



step height: 0.4 nm

### **STEM: Cross Section**

HAADF

LAADF



L. Fitting-Kourkoutis, D.A. Muller (Cornell)

### Interface Conductance vs Number of LaAIO3 Unit Cells





critical thickness

$$d_{\rm c}=4~{\rm uc}$$

S. Thiel *et al.*, Science **313**, 1942 (2006)

# Pattern Containing q2-DEG



C.W. Schneider et al., Appl. Phys. Lett. 89, 122101 (2006)

### Low Temperature Transport of the Electron Gas



N. Reyren, J.-M. Triscone et al., submitted

### Upper Limit to the Thickness of the Superconducting Sheet

 $> T_c = 200 \text{ mK} \rightarrow n \gtrsim 3 \times 10^{19} / \text{cm}^3$ 



C.S. Koonce, M.L. Cohen *et al.*, PRL **163**, 380 (1967)

> Hall measurements:  $n_{\rm S} \simeq 3 \times 10^{13} / \rm{cm}^2$ 

link to Cohen, Geballe

### Tuning T<sub>c</sub> with Gate Voltages



N. Reyren et al., to be published

### Upper Limit to the Thickness of the Superconducting Sheet

overdoped  $\rightarrow n \gtrsim 9 \times 10^{19} / \text{cm}^3$ 



C.S. Koonce, M.L. Cohen *et al.*, PRL **163**, 380 (1967)

> Hall measurements:  $n_{\rm S} \simeq 3 \times 10^{13} / \rm{cm}^2$ 

link to Cohen, Geballe



### Insulating Layers at High- $T_c$ Grain Boundaries



link to Gurevich

J. Mannhart and H. Hilgenkamp, Supercond. Sci. Technol. <u>10</u>, 880 (1997)

### Insulating Layers at High- $T_c$ Grain Boundaries



J. Mannhart and H. Hilgenkamp, Supercond. Sci. Technol. <u>10</u>, 880 (1997)

### **Proposal: Boosting** *T*<sub>c</sub> with second phases:

- inducing correlations at interfaces
- > providing pairing interactions
- doping the interfaces
- generating electric and magnetic fields
- generating stress/strain at interface
- extending stability range of superconducting phase

link to Chu, Bozovich

*T*<sub>c</sub>-booster phase interface with high *T*<sub>c</sub> standard low *T*<sub>c</sub> superconductor

### Searching for the Preferable Mesoscopic Structure

Phase coherence problem :

 $E_{\rm J} = \frac{\hbar I_{\rm c}}{2e}$ 

 $d=10\,\mathrm{nm},\,w=10\,\mu\mathrm{m}$ 



- $\rightarrow J_{\rm c}(300\,{\rm K}) \ge 10^6\,{\rm A/cm}^2$  required for  $R(300\,{\rm K}) \approx 0$
- $\rightarrow$  mesoscopic structure requires interfaces connected in parallel

links to Beasley, Gurevich

### Searching for the Preferable Mesoscopic Structure

cross-sections:





small *c*-axis coupling

problematic for anisotropic superconductors

length scales: correlation lengths,  $\lambda_{el}$ ,  $\xi$ , ...

→ mesoscopic structure required

### Searching for the Preferable Mesoscopic Structure



structure of some early HTS USOs?



(superconducting) matrix: HTS, organics, whatever ...



 $T_c$  booster phase



interfaces with boosted  $T_c$ 

effectively percolating

### How to Grow the Hybrid-Structures?



A. Catana et al., Appl. Phys. Lett. 60, 1016 (1992)

The growth problem of interest for a spectrum of applications

first industrial solutions for the growth of nano-scale inclusions in coated conductors

link to Gurevich

### Analogon: III-V Heterostructures





AlGaAs/GaAs-HEMT

S.M. Sze: "High Speed Semiconductor Devices"

### Mobile Electrons at Interfaces of Complex Materials



### Conclusion:

Use Mesoscopic Structure to Enhance T<sub>c</sub>

- > Kresin Effect: nanoclusters with number of electrons close to magic
- For superconductors that like a self-organized internal structure: add matching microstructure
- > "Hybrid" superconductors to gain a high- $T_c$  at interfaces

### Conclusion:

- "Hybrid" Superconductors:
- superconducting matrix
- $\succ$  second phase to enhance  $T_c$  of interface layers
- > optimization of the mesoscopic structure

*T*<sub>c</sub>-booster phase -interface with high *T*<sub>c</sub> -standard low *T*<sub>c</sub> superconductor



Road to higher T<sub>c</sub>'s?